

GP1M006A065FH

GP1M006A065FH Information

www.helsener.com	 GP1M006A065FH Global Power Technologies Group Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 650V 5.5A TO220F TO-220-3 Full Pack For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



GP1M006A065FH Specifications

Manufacturer Part Number	GP1M006A065FH
Manufacturer	Global Power Technologies Group
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3 Full Pack
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	650V
Current - Continuous Drain (Id) @ 25°C	5.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1177pF @ 25V
Vgs (Max)	±30V
FET Feature	-
Power Dissipation (Max)	39W (Tc)
Rds On (Max) @ Id, Vgs	1.6 Ohm @ 2.75A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-220F
Package / Case	TO-220-3 Full Pack
	Report errors?

GP1M006A065FH Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

GP1M006A065FH Payment Methods





If you have any question about GP1M006A065FH, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com